TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8047-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 13 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS(ON)} = 4.8 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 92 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.5 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

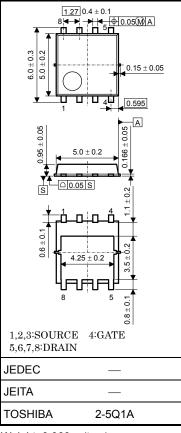
| Characte              | eristic                       | Symbol           | Rating     | Unit |  |
|-----------------------|-------------------------------|------------------|------------|------|--|
| Drain-source voltage  |                               | V <sub>DSS</sub> | 40         | V    |  |
| Drain-gate voltage (R | $R_{GS} = 20 \text{ k}\Omega$ | V <sub>DGR</sub> | 40         | V    |  |
| Gate-source voltage   |                               | V <sub>GSS</sub> | ±20        | V    |  |
|                       | DC (Note 1)                   | ۱ <sub>D</sub>   | 32         |      |  |
| Drain current         | Pulsed (Note 1)               | IDP              | 96         | A    |  |
| Drain power dissipati | on (Tc = 25°C)                | PD               | 45         | W    |  |
| Drain power dissipati | on (t = 10 s)<br>(Note 2a)    | PD               | 2.8        | W    |  |
| Drain power dissipati | on (t = 10 s)<br>(Note 2b)    | PD               | 1.6        | W    |  |
| Single-pulse avalance | he energy<br>(Note 3)         | E <sub>AS</sub>  | 95         | mJ   |  |
| Avalanche current     |                               | I <sub>AR</sub>  | 32         | Α    |  |
| Repetitive avalanche  | energy<br>c = 25°C) (Note 4)  | E <sub>AR</sub>  | 3.95       | mJ   |  |
| Channel temperature   | 1                             | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature   | range                         | T <sub>stg</sub> | –55 to 150 | °C   |  |

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

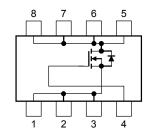
reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

## **Circuit Configuration**

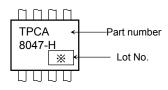


Unit: mm

#### **Thermal Characteristics**

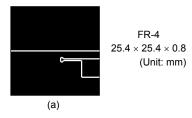
| Characteristic   | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case<br>(Tc = 25°C)             | R <sub>th (ch-c)</sub> | 2.78 | °C/W |
| Thermal resistance, channel to ambient<br>(t = 10 s) (Note 2a) | R <sub>th (ch-a)</sub> | 44.6 | °C/W |
| Thermal resistance, channel to ambient<br>(t = 10 s) (Note 2b) | R <sub>th (ch-a)</sub> | 78.1 | °C/W |

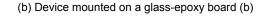
#### Marking (Note 5)

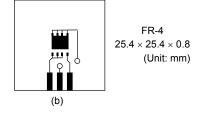


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)







Note 3:  $V_{DD} = 24 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 100  $\mu$ H, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 32 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



Week of manufacture \_ (01 for the first week of the year, continuing up to 52 or 53) – Year of manufacture

(The last digit of the year)

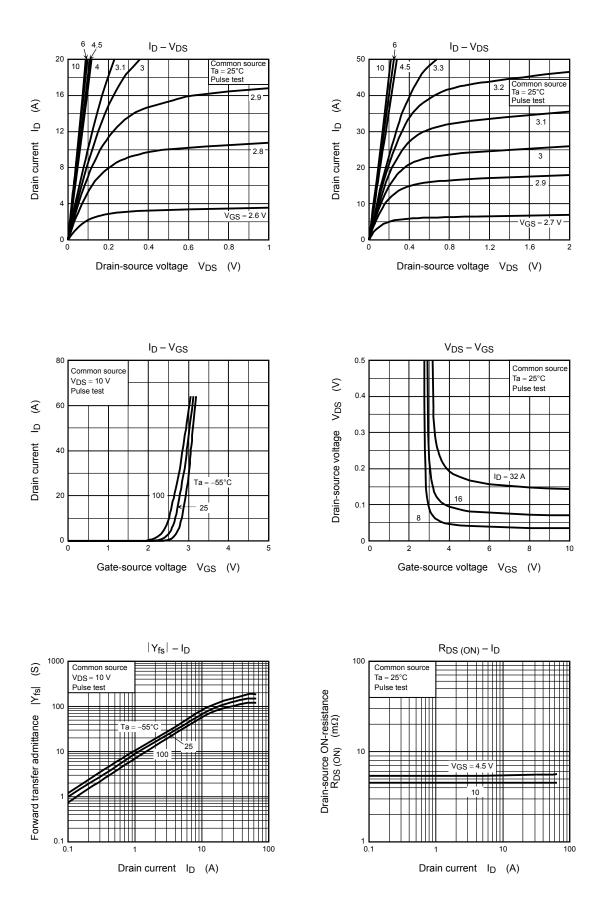
## **Electrical Characteristics (Ta = 25°C)**

| Characteristic                 |  | Symbol               | Test Condition   | Min | Тур. | Max  | Unit |
|--------------------------------|--|----------------------|--|-----|------|------|------|
| Gate leakage cur               | rent   | I <sub>GSS</sub>     | $V_{GS}=\pm 20~V,~V_{DS}=0~V$  | _   | —    | ±100 | nA   |
| Drain cutoff curre             | nt   | I <sub>DSS</sub>     | $V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$                                      |     | _    | 10   | μA   |
| Drain-source breakdown voltage |  | V (BR) DSS           | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$  | 40  | —    |      | V    |
|                                |  | V (BR) DSX           | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$  | 25  | _    |      |      |
| Gate threshold vo              | oltage   | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.5 \text{ mA}$                                    | 1.3 | _    | 2.3  | V    |
| Drain-source ON-resistance     |  | Deckern              | $V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$   |     | 6.0  | 8.5  | -mΩ  |
|                                |  | R <sub>DS</sub> (ON) | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 16 \text{ A}$                                      |     | 4.8  | 7.3  |      |
| Forward transfer               | ard transfer admittance $ Y_{fs} $ $V_{DS} = 10 \text{ V}, I_D = 16 \text{ A}$ |                      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 16 \text{ A}$                                      | 46  | 92   |      | S    |
| Input capacitance              |  | C <sub>iss</sub>     |  | _   | 2590 | 3365 | pF   |
| Reverse transfer capacitance   |  | C <sub>rss</sub>     | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1 MHz   |     | 135  | 200  |      |
| Output capacitance             |  | C <sub>oss</sub>     |  | _   | 440  |      |      |
| Gate resistance                |  | rg                   | $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$           | _   | 1.0  | 1.5  | Ω    |
| Switching time                 | Rise time  | tr                   | $V_{GS} \stackrel{10}{}_{0}V \prod I_{D} = 16 \text{ A}$                                   | _   | 4.8  | _    | ns   |
|                                | Turn-on time   | t <sub>on</sub>      |  | _   | 13   | _    |      |
|                                | Fall time  | t <sub>f</sub>       |  | _   | 9.9  | _    |      |
|                                | Turn-off time  | t <sub>off</sub>     | $V_{DD}\approx 20~V$ Duty $\leq$ 1%, $t_W=10~\mu s$  | _   | 43   | _    |      |
| Total gate charge              |  | Qg                   | $V_{DD} \approx 32 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 32 \text{ A}$ |     | 43   |      |      |
| (gate-source plus              | gate-source plus gate-drain)   |                      | $V_{DD}\approx 32~V,~V_{GS}=5~V,~I_{D}=32~A$   |     | 23   |      |      |
| Gate-source charge 1           |  | Q <sub>gs1</sub>     | $V_{DD} \approx 32 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 32 \text{ A}$ |     | 7.9  |      | nC   |
| Gate-drain ("Miller") charge   |  | Q <sub>gd</sub>      |  | _   | 8.4  |      | -    |
| Gate switch charge             |  | Q <sub>SW</sub>      | ]  |     | 13   |      |      |

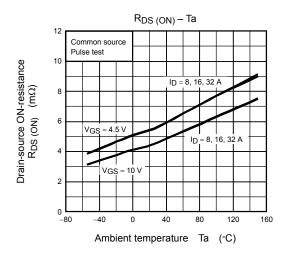
## Source-Drain Ratings and Characteristics (Ta = 25°C)

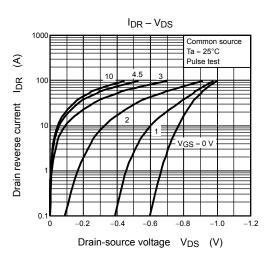
| Characteristic          |       | Symbol   | Test Condition   | Min                       | Тур. | Max | Unit |   |
|-------------------------|-------|----------|------------------|---------------------------|------|-----|------|---|
| Drain reverse current   | Pulse | (Note 1) | I <sub>DRP</sub> | —                         | _    |     | 96   | А |
| Forward voltage (diode) |       |          | VDSF             | $I_{DR}=32~A,~V_{GS}=0~V$ | _    | _   | -1.2 | V |

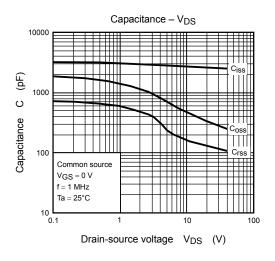
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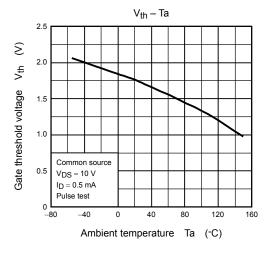


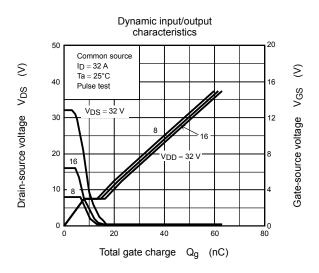
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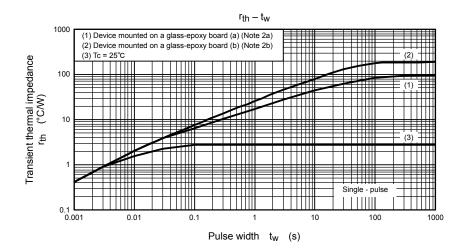


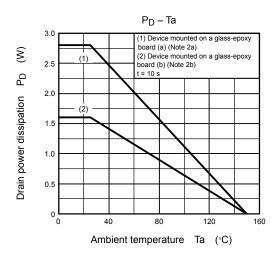


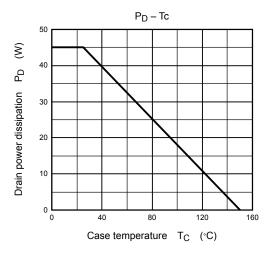


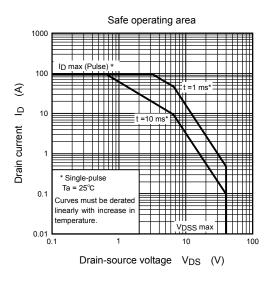












# <u>TOSHIBA</u>

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